

Applicants respectfully request the following amendments in support of the following remarks.

Please amend the application as follows:

IN THE SPECIFICATION:

On page 1, lines 7-10 amend the related application information paragraph as follows:

Related Application

a1 This application is related to pending United States Patent Application Serial Number 09/122,710, entitled "Method of Forming A Semiconductor Device", now U.S. Patent 6,297,169 issued on October 2, 2001, filed by Pawitter Mangat et al. on July 27, 1998 and assigned to the assignee hereof.

IN THE CLAIMS:

Please amend the claims as follows. For the convenience of the Examiner, all pending claims, whether amended or not, are presented.

- a2 SUB B1
1. (Currently Amended) A thin membrane stencil mask, comprising:
- a substrate having a primary surface and a secondary surface opposite the primary surface;
 - a thin membrane layer overlying the primary surface of the substrate;
 - a stress control layer overlying the thin membrane layer;
 - an ion absorbing layer overlying the stress control layer for absorbing radiation ions to improve material stability of the stress control layer and the thin membrane layer;
 - one or more cavities in the substrate extending from the secondary surface to the thin membrane layer; and